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Yayi Wei received his Masters Degree in Engineering from the Electronics Institute, Chinese Academy of Sciences, Beijing, China in 1992 and his Doctorate (Doktor der Naturwissenschaften) from the Max Planck Institute for Solid State Research, Stuttgart, Germany in 1998. As a graduate student in the Max Planck Institute for Solid State Research, Dr. Wei specialized in the electronic transportation of low-dimensional structures and microfabrications. After receiving his Doctorate, Dr. Wei worked for Oak Ridge National Laboratory (ORNL) on electron-beam lithography and nanofabrications; Infineon Technologies, which later became Qimonda, on the process development and material evaluation of advanced lithography in 193-, 157-, and 193-nm immersion, as well as EUV; and AZ Electronic Materials on lithographic materials applications. Dr. Wei has numerous publications and holds several patents in the field of lithography.

Robert L. Brainard received his B.S. in Chemistry from U.C. Berkeley in 1979. He synthesized and studied the reaction mechanisms of organoplatinum compounds during his graduate studies with George Whitesides at MIT and Harvard University. After receiving his Ph.D. in 1985, he studied the reaction mechanisms on copper and silver surfaces under ultrahigh vacuum conditions as a post-doctoral student at Stanford University. Robert worked for Polaroid 1987–1990, where he developed new gold and sulfur chemistry for use in the chemical sensitization of silver halide photographic emulsions. He worked at Shipley/Rohm & Haas 1990–2005, where he did product development research in the areas of: electrodeposited, dielectric, color filter, DUV, EUV, x-ray and e-beam photoresists. Robert is now an Associate Professor at the College of Nanoscale Science and Engineering, UAlbany, investigating new materials for use in EUV and 193-nm lithography.

(Photo of Robert Brainard by Mia Ertas, UAlbany College of Nanoscale Science and Engineering.)